AO4435A

P Channel Enhancement Mode MOSFET

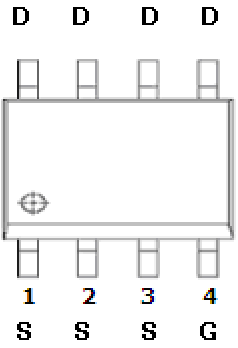
深圳市芯创世纪电子有限公司

-10A

DESCRIPTION

AO4435A is the P-Channel logic enhancement mode power field effect transistor which is produced using high cell density, DMOS trench technology. This high density process is especially tailored to minimize on-state resistance. These devices are particularly suited for low voltage application such as LCD backlight, notebook computer power management, and other battery powered circuits.

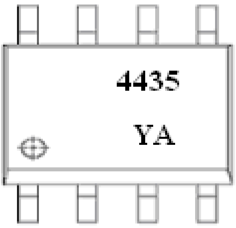
PIN CONFIGURATION
SOP-8



FEATURE

- -30V/-9.2A, $R_{DS(ON)}$ = 22mΩ (Typ.) @V_{GS} =-10V
- -30V/-7.0A, $R_{DS(ON)}$ = 30mΩ @V_{GS} = -4.5V
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- SOP-8 package design

PART MARKING
SOP-8



Y: Year Code A: Process Code